wherein said laser beam has an irradiation area of said pulsed laser beam of 10 cm^2 or more.

3. (Amended) A method of manufacturing a semiconductor device, comprising:

a first step of forming a semiconductor film on a substrate having an insulating surface;

a second step of holding a catalytic element that promote the crystallization of said semiconductor film in contact with said semiconductor film; and

a third step of irradiating a laser beam shaped in a rectangle or a square from one side of said semiconductor film toward another side thereof while moving said substrate to sequentially crystallize said semiconductor film to form a crystalline semiconductor film,

wherein said laser beam has an irradiation area of said pulsed laser beam of 10 cm^2 or more.

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9. (Amended). A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein a pulse width of the laser beam irradiated in the third step is 600 nsec to 1 msec.

10. (Amended) A method of manufacturing a semiconductor device as claimed in claim 1, 2, 3, 4, 5, 6 or 8, wherein a laser energy density of the laser beam irradiated in the third step is 100 to 800 mJ/cm^2.

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20. (Amended). A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

providing said semiconductor film with a crystallization promoting material comprising a metal;

crystallizing said semiconductor film by irradiating said semiconductor film with a pulsed laser beam,

wherein said laser beam has a pulse width of 200 nsec or more,